

Silicon NPN Power Transistors

2SD1677

DESCRIPTION

- With TO-3PN package
- High breakdown voltage
- High reliability
- Fast speed

APPLICATIONS

- For TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

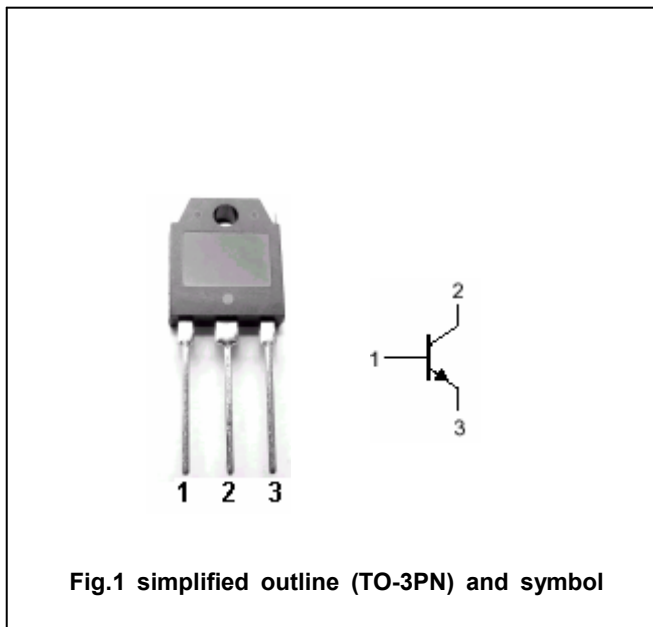


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
P _C	Collector power dissipation	T _a =25□	2.5	W
		T _C =25□	100	
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A ; I _B =2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =5V	8			

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PACKAGE OUTLINE

